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(54) **SEMICONDUCTOR DEVICE WITH STACKED SEMICONDUCTOR CHIPS**

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(58) **Field of Classification Search**

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USPC ..... 257/686, 777, E23.141, E23.085  
See application file for complete search history.

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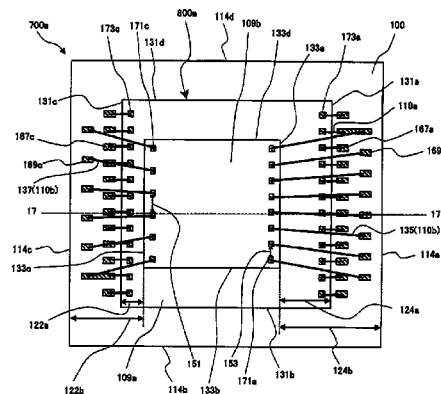
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Primary Examiner — Tucker Wright

(57) **ABSTRACT**

A semiconductor chip **109** is mounted on a substrate **100**, first wire group **120** and a second wire group **118** having a wire length shorter than the first wire group are provided so as to connect the substrate **100** and the semiconductor chip **109** to each other, and a sealing resin **307** is injected from the first wire group **120** toward the second wire group **118** so as to form a sealer **401** covering the semiconductor chip **109**, the first wire group **120**, and the second wire group **118**.

**8 Claims, 12 Drawing Sheets**



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**H01L 23/31** (2006.01)

**H01L 23/498** (2006.01)

(52) **U.S. Cl.**

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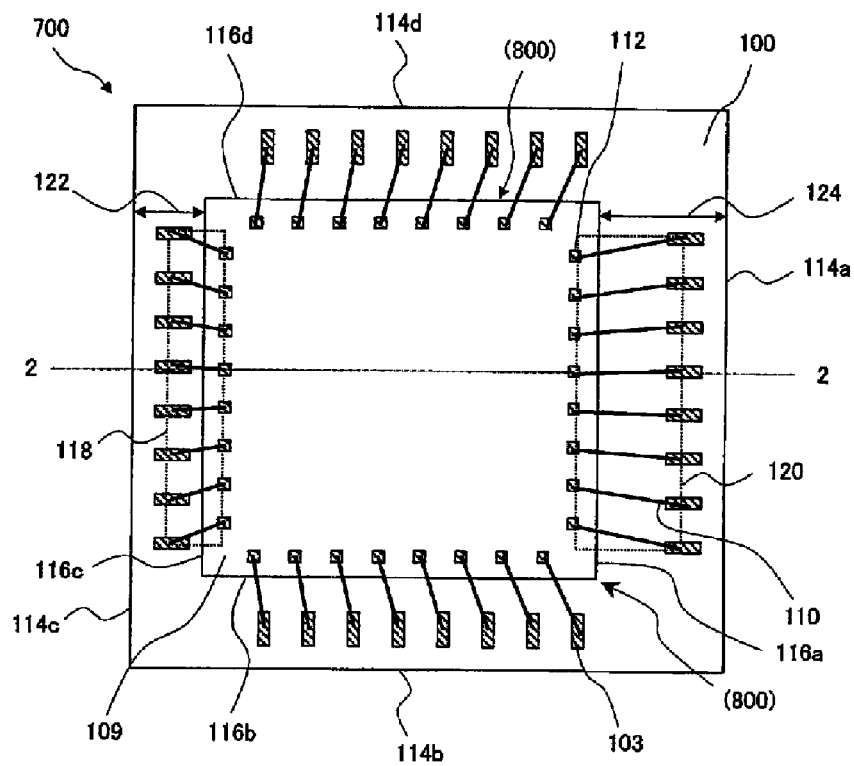


FIG. 1

FIG. 2

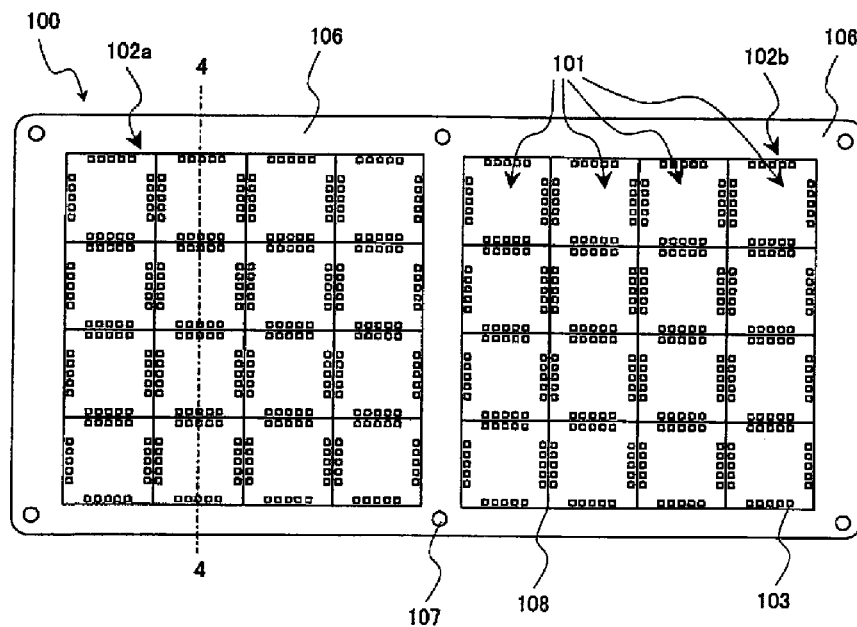


FIG. 3

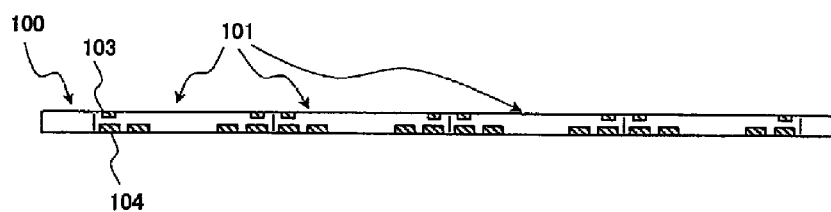


FIG. 4

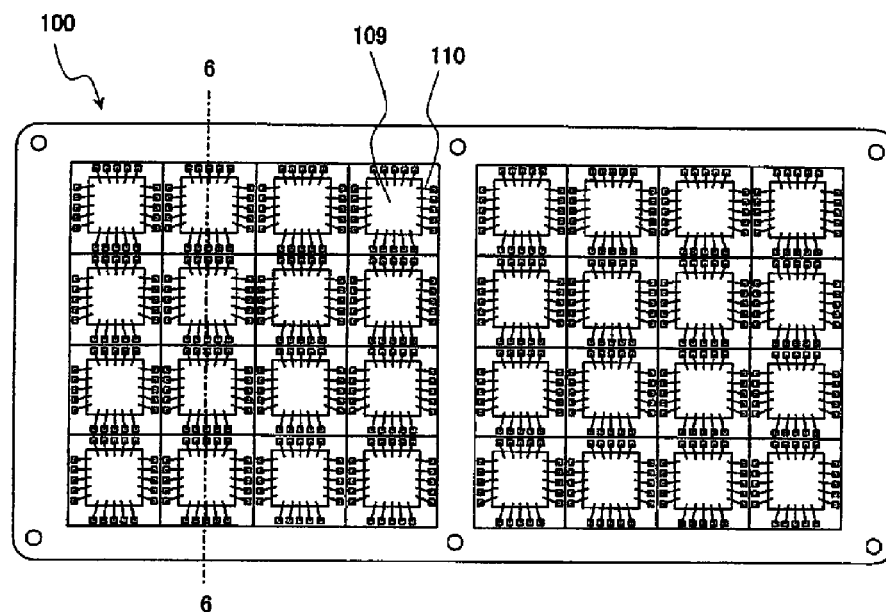


FIG. 5

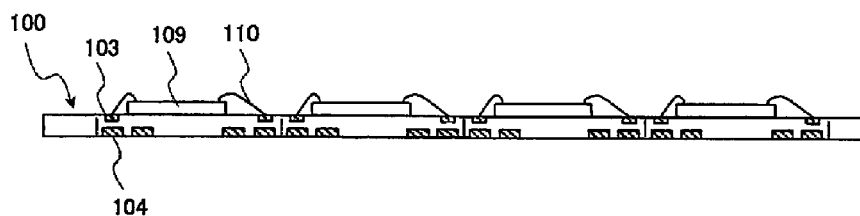


FIG. 6

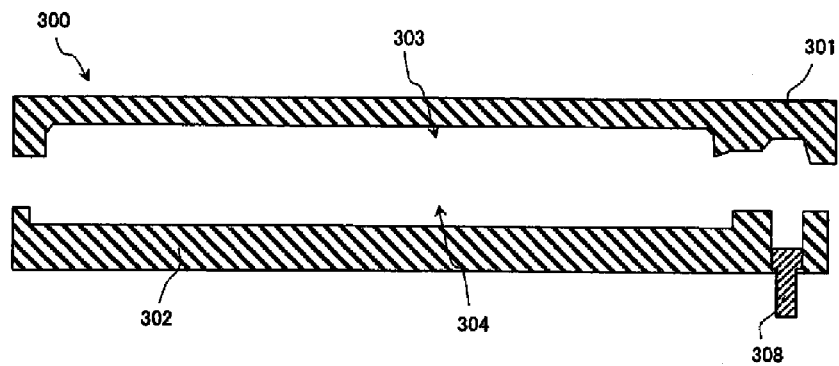


FIG. 7

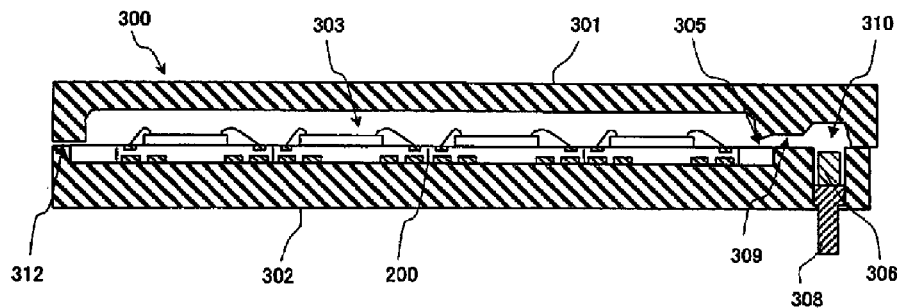


FIG. 8

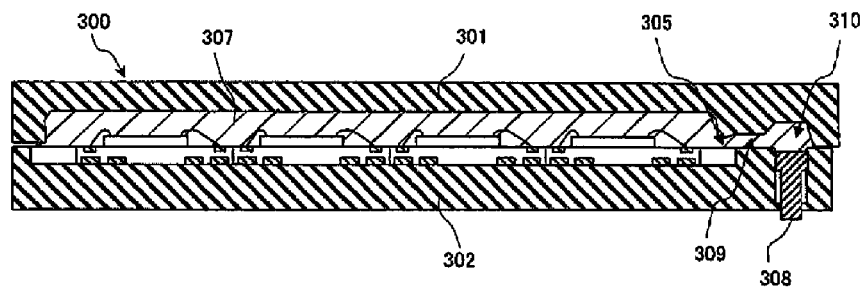


FIG. 9

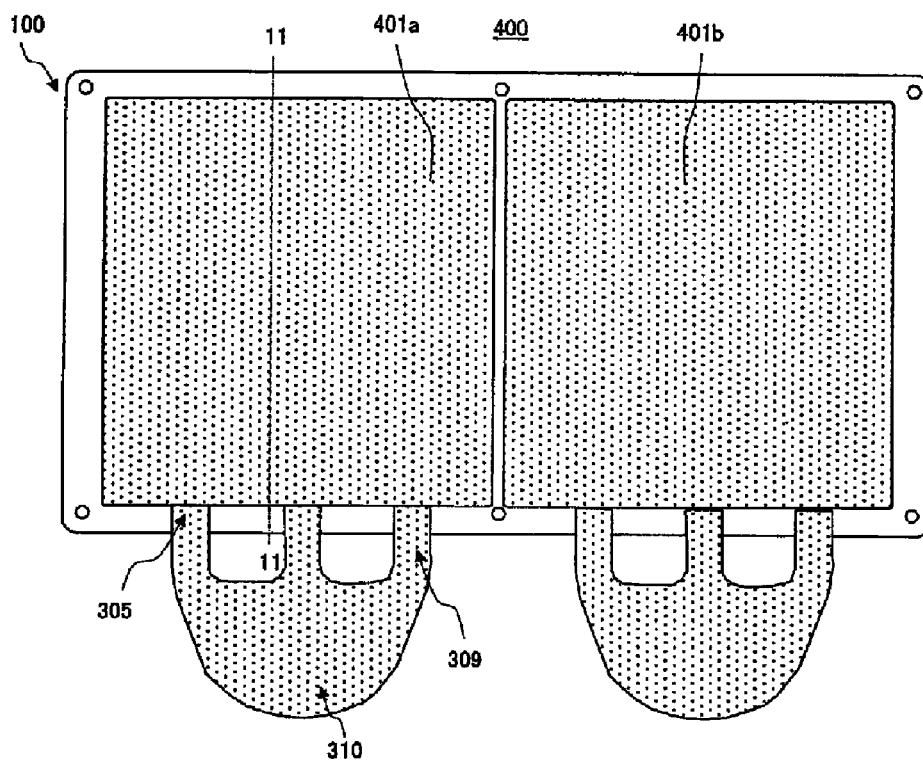


FIG. 10

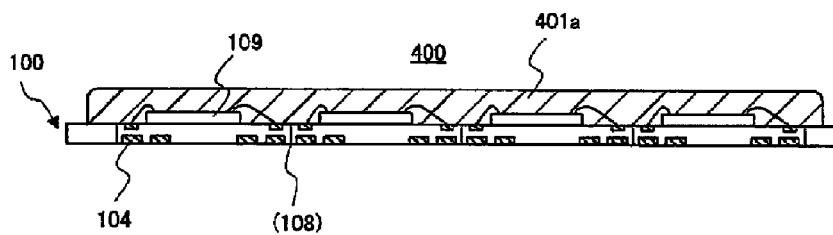


FIG. 11



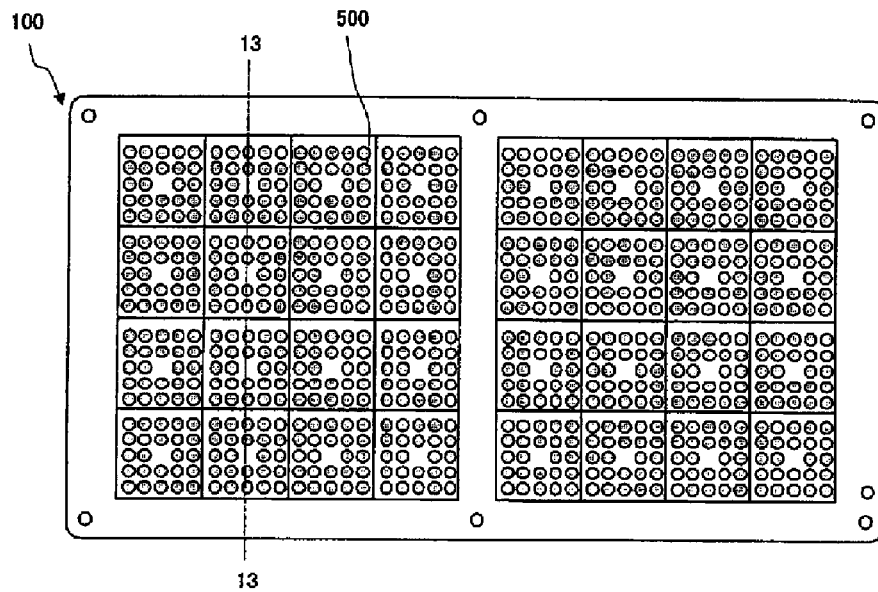


FIG. 12

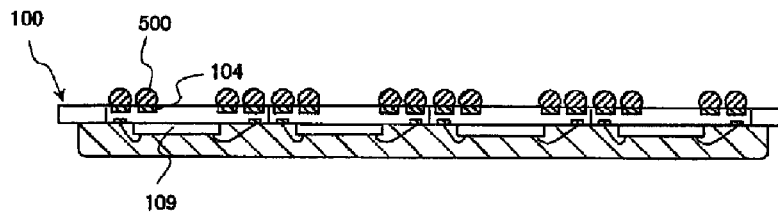


FIG. 13

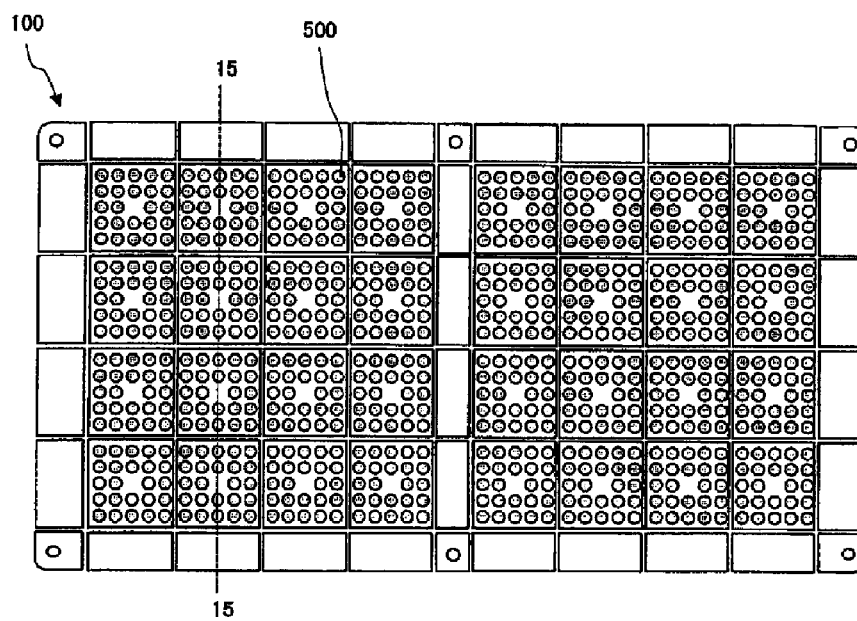


FIG. 14

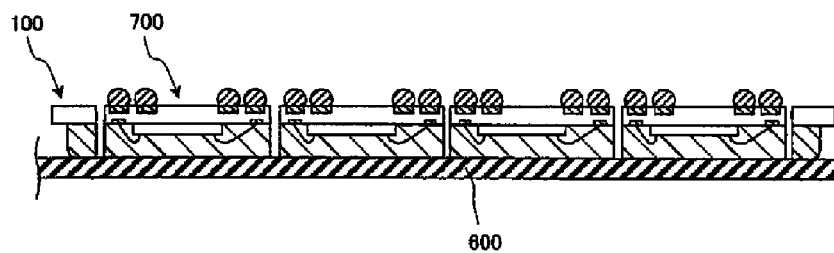


FIG. 15

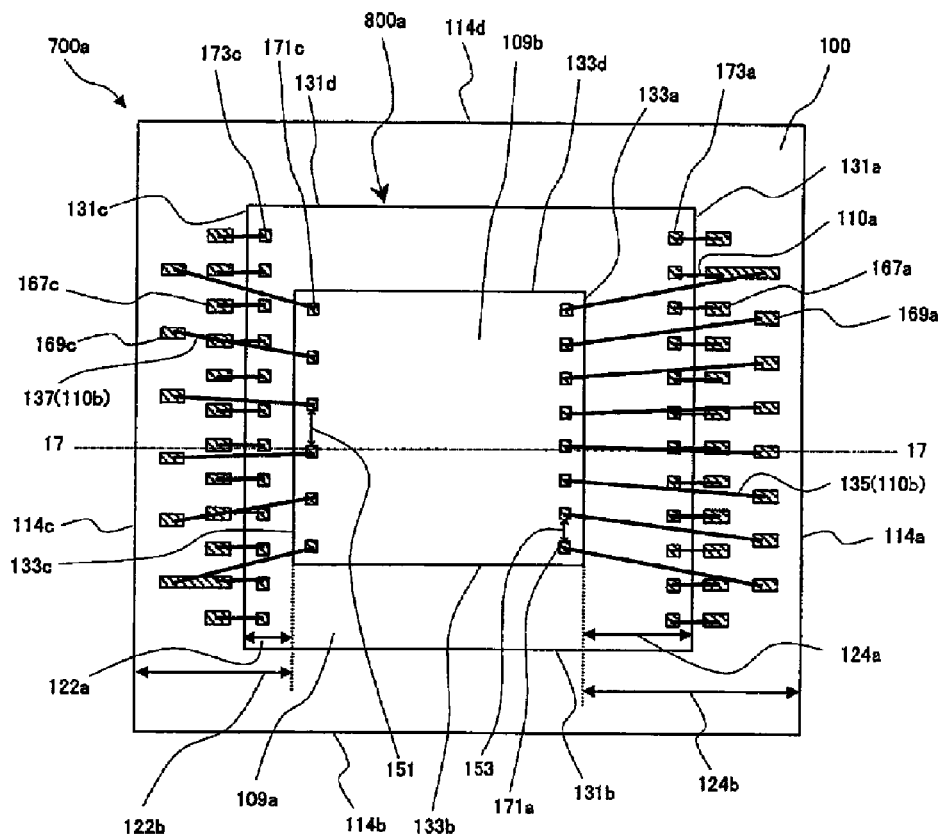


FIG. 16

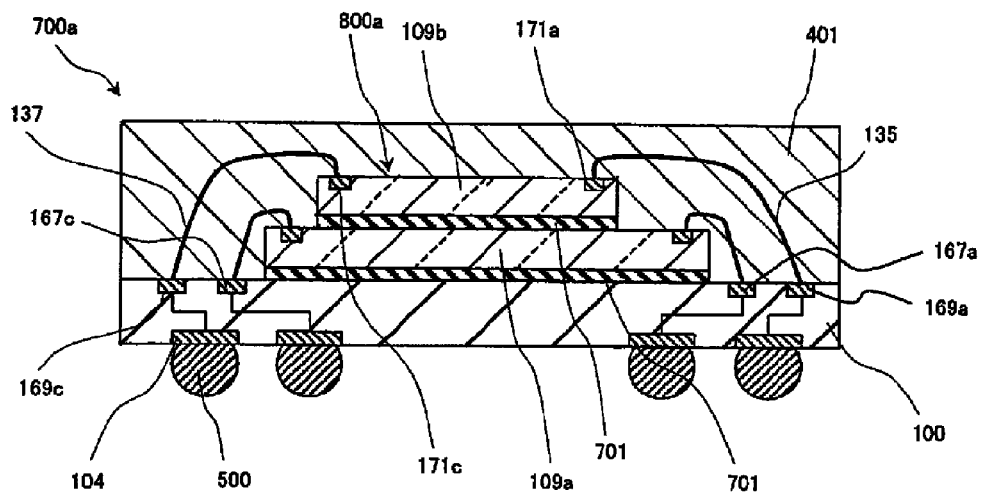


FIG. 17

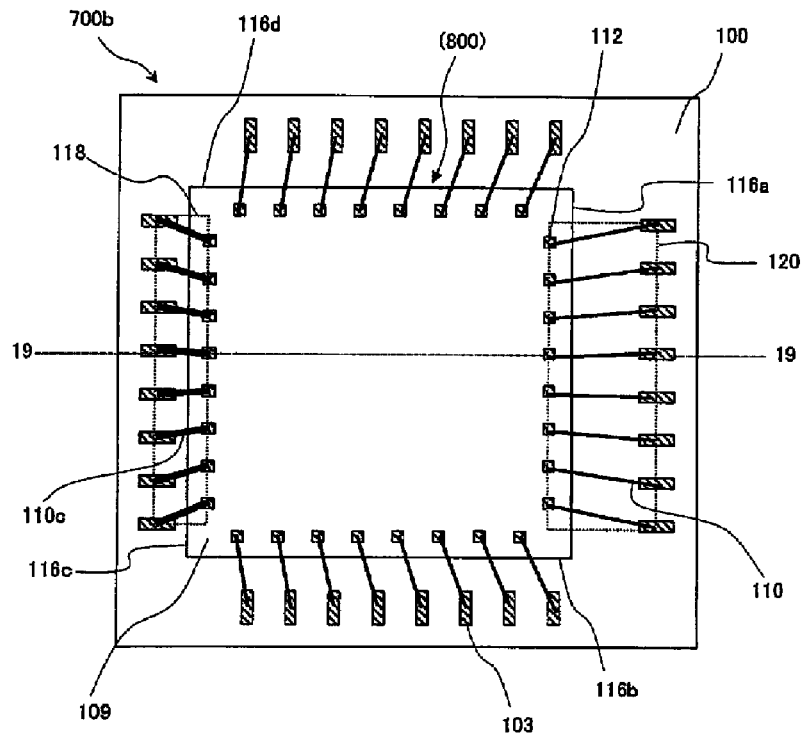


FIG. 18

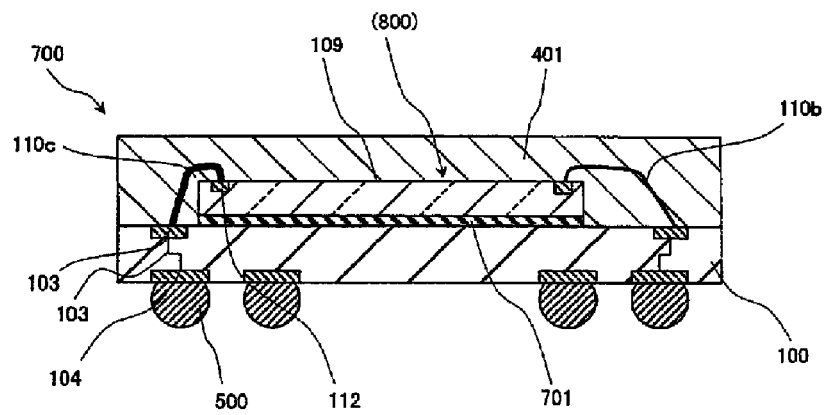


FIG. 19

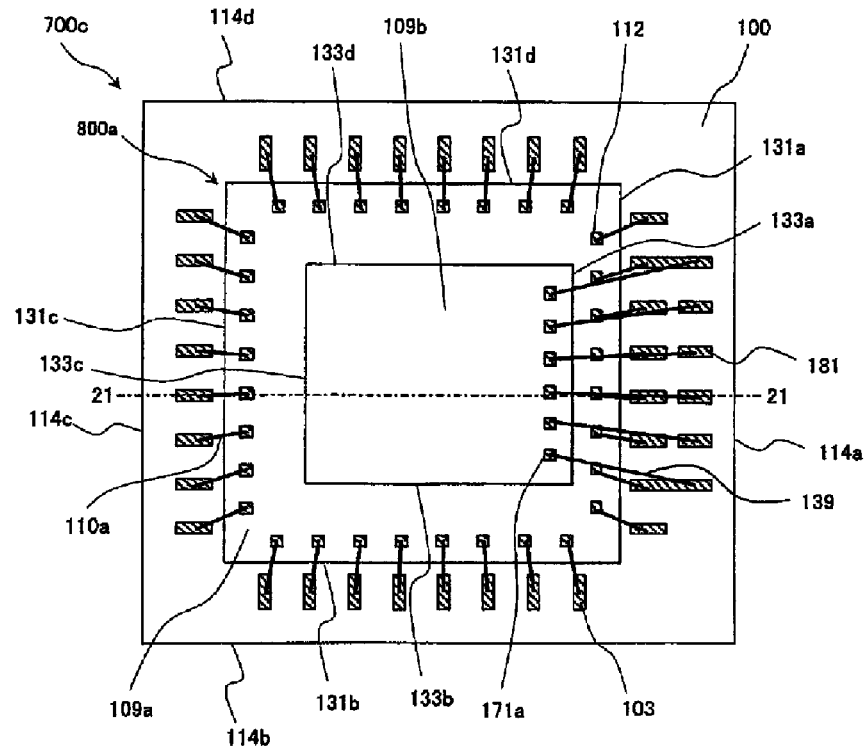


FIG. 20

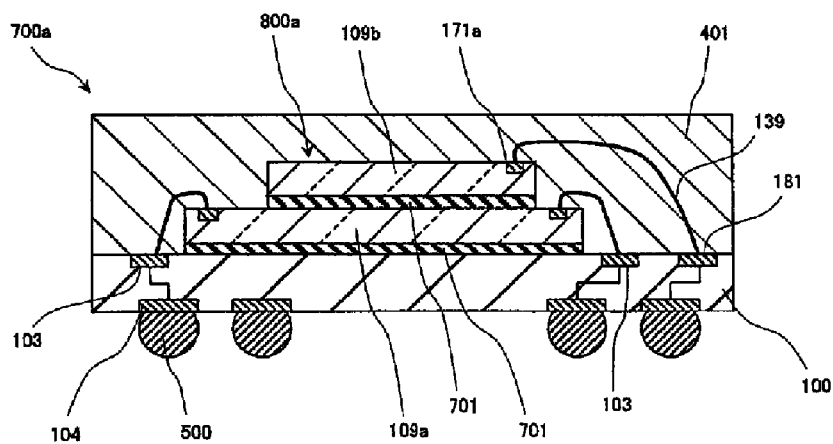


FIG. 21

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# SEMICONDUCTOR DEVICE WITH STACKED SEMICONDUCTOR CHIPS

## CROSS REFERENCE TO RELATED APPLICATIONS

This application is a continuation of application Ser. No. 12/898,198 filed on Oct. 5, 2010, which claims the benefit of priority from Japanese Patent Application No. 2010-099436, filed on Apr. 23, 2010. The entire contents of each of the above applications are hereby incorporated by reference.

## BACKGROUND OF THE INVENTION

### 1. Field of the Invention

The present invention relates to a method of manufacturing a semiconductor device and a semiconductor device.

### 2. Description of Related Art

As disclosed in Japanese laid-open patent publications No. 2001-44229 (Patent Document 1) and 2001-44324 (Patent Document 2), methods of manufacturing a ball grid array type (BGA) semiconductor device include a mold array process (MAP), which comprises preparing a substrate having a plurality of product formation portions, mounting semiconductor chips on each of the product formation portions, forming a sealer so that the sealer integrally covers the product formation portions on the substrate, and dividing the substrate into the individual product formation portions.

## SUMMARY

However, according to the MAP type method of manufacturing a semiconductor device, a sealing resin is injected from gates along a direction perpendicular to one side of semiconductor chips. Therefore, an entrainment occurs at another side of the semiconductor chips (near air vents) that is opposite to the side from which the resin is injected. Thus, the flow rate of the resin flowing near the air vents is higher than that of the resin flowing on the side from which the resin is injected.

As a result, a wire sweep may occur on wires provided near the air vents due to the pressure of the injected resin. Furthermore, wires may be brought into contact with each other to cause a short circuit.

The present invention seeks to solve one or more of the above problems, or to improve upon those problems at least in part.

In one embodiment, there is provided a method of manufacturing a semiconductor device, the method comprising: (a) mounting a semiconductor chip set comprising at least one semiconductor chip on a substrate; (b) providing a first wire group and a second wire group having a wire length shorter than the first wire group so as to connect the substrate and the at least one semiconductor chip to each other; and (c) injecting a sealing resin from the first wire group toward the second wire group so as to form a sealer covering the at least one semiconductor chip, the first wire group, and the second wire group.

In another embodiment, there is provided a semiconductor device comprising: a substrate; a semiconductor chip set including at least one semiconductor chip mounted on the substrate; a first wire group and a second wire group provided so as to connect the substrate and the semiconductor chip set to each other, the second wire group having a wire length shorter than that of the first wire group; and a sealer covering the at least one semiconductor chip set, the first wire group, and the second wire group.

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## BRIEF DESCRIPTION OF THE DRAWINGS

The above features and advantages of the present invention will be more apparent from the following description of certain preferred embodiments taken in conjunction with the accompanying drawings, in which:

FIG. 1 is a plan view (top view) showing a semiconductor device, in which a sealer is illustrated as being transparent;

FIG. 2 is a cross-sectional view taken along line 2-2 of FIG. 1;

FIG. 3 is a diagram showing a general configuration of a substrate manufacturing a semiconductor device;

FIG. 4 is a cross-sectional view taken along line 4-4 of FIG. 3;

FIG. 5 is a plan view explanatory of a wire bonding process;

FIG. 6 is a cross-sectional view taken along line 6-6 of FIG. 5;

FIG. 7 is a cross-sectional view showing a general configuration of a molding apparatus (transfer molding apparatus) sealing a semiconductor device;

FIG. 8 is a cross-sectional view explanatory of a sealing process;

FIG. 9 is a cross-sectional view explanatory of the sealing process;

FIG. 10 is a plan view showing an intermediate structure;

FIG. 11 is a cross-sectional view taken along line 11-11 of FIG. 10;

FIG. 12 is a plan view explanatory of a ball mounting process;

FIG. 13 is a cross-sectional view taken along line 13-13 of FIG. 12;

FIG. 14 is a plan view explanatory of a substrate dicing process;

FIG. 15 is a cross-sectional view taken along line 15-15 of FIG. 14;

FIG. 16 is a plan view (top view) showing a semiconductor device according to another embodiment of the present invention, in which a sealer is illustrated as being transparent;

FIG. 17 is a cross-sectional view taken along line 17-17 of FIG. 16;

FIG. 18 is a plan view (top view) showing a semiconductor device according to still another embodiment of the present invention, in which a sealer is illustrated as being transparent;

FIG. 19 is a cross-sectional view taken along line 19-19 of FIG. 18;

FIG. 20 is a plan view (top view) showing a semiconductor device according to still another embodiment of the present invention, in which a sealer is illustrated as being transparent; and

FIG. 21 is a cross-sectional view taken along line 21-21 of FIG. 20.

## DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

The invention will be now described herein with reference to illustrative embodiments. Those skilled in the art will recognize that many alternative embodiments can be accomplished using the teachings of the present invention and that the invention is not limited to the embodiments illustrated for explanatory purposes.

Preferred embodiments of the present invention will be described below with reference to FIGS. 1 to 21.

First, a general configuration of a semiconductor device 700 according to a first embodiment of the present invention will be described with reference to FIGS. 1 and 2.

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As shown in FIGS. 1 and 2, the semiconductor device 700 comprises a substrate 100 in the form of a plate and a semiconductor chip 109 mounted on one surface of the substrate 100 via an adhesive portion 701, such as an adhesive agent or a die attached film (DAF). The substrate 100 has a polygonal shape (a rectangular shape herein) on the plane. The semiconductor chip 109 has a polygonal shape (a rectangular shape herein) on the plane.

The semiconductor chip 109 comprises a logical circuit such as a microprocessor or a memory circuit such as a static random access memory (SRAM) or a dynamic random access memory (DRAM) formed on a substrate such as silicon or germanium. The semiconductor chip 109 includes electrode pads 112 on its front face, which is opposite to the adhesive surface.

A passivation film (not shown) is formed on the front face of the semiconductor chip 109 except the electrode pads 112. Thus, the surface on which the circuits have been formed is protected.

In FIG. 1, only one semiconductor chip 109 is mounted on the substrate 100. This single semiconductor chip 109 constitutes a semiconductor chip set 800. Nevertheless, the semiconductor device may include a plurality of chips as described later.

The substrate 100 includes connection pads 103 provided on a surface thereof on which the semiconductor chip 109 is mounted, lands 104 provided on another surface thereof, and internal wiring lines 105 for connecting the connection pads 103 and the lands 104 to each other.

For example, the substrate 100 is formed of a glass epoxy substrate.

Solder balls 500 are formed as external terminals (bump electrodes) on the lands 104 connecting the semiconductor device 700 to other devices. The connection pads 103 are electrically connected to the electrode pads 112 by wires 110.

Specifically, the semiconductor chip 109 is connected to the solder balls 500 via the electrode pads 112, the wires 110, the connection pads 103, the internal wiring lines 105, and the lands 104.

A wiring pattern (not shown) is formed on the surface of the substrate 100. Areas other than those comprising the connection pads 103 and the lands 104 are covered with an insulating film (not shown), such as a solder resist.

Furthermore, the semiconductor device 700 is provided with a sealer 401 so that the sealer 401 covers at least the semiconductor chip 109, the connection pads 103, the electrode pads 112, and the wires 110.

The sealer 401 is formed of a thermosetting resin having insulating properties, such as an epoxy resin. The sealer 401 serves to protect the semiconductor chip 109 and the electrically connected portions such as the connection pads 103, the electrode pads 112, and the wires 110.

The shapes and arrangements of the wires 110, the substrate 100, and the semiconductor chip 109 will be described below.

As described above, the semiconductor chip 109 has a rectangular shape on the plane. As shown in FIG. 1, the semiconductor chip 109 has a side 116a (first side), a side 116b, a side 116c (second side), and a side 116d.

Furthermore, the substrate 100 also has a rectangular shape on the plane. As shown in FIG. 1, the substrate 100 has a side 114a (third side), a side 114b, a side 114c (fourth side), and a side 114d.

The electrode pads 112 are arranged along the sides 116a, 116b, 116c, and 116d. The connection pads 103 are also arranged along the sides 114a, 114b, 114c, and 114d.

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The wires 110 are provided so as to stride across the sides 116a, 116b, 116c, and 116d, respectively.

A first wire group 120 and a second wire group 118 are provided so as to respectively stride across the sides 116a and 116c, which are opposed to each other. The wire length of the second wire group 118 is shorter than that of the first wire group 120.

Thus, the wires striding across one of the opposing sides are shortened as compared to the wires striding across the other side. A wire sweep or a wire short circuit due to an injected resin can be prevented when a resin is injected from the side of the long wires toward the side of the short wires, the details of which will be described later.

Meanwhile, the sides 116a, 116b, 116c, and 116d of the semiconductor chip 109 are provided so as to correspond to the sides 114a, 114b, 114c, and 114d of the substrate 100, respectively. The shortest distance 122 between the side 114c and the side 116c is shorter than the shortest distance 124 between the side 114a and the side 116a.

When the semiconductor chip 109 is located at such a position, the wire length of the second wire group 118 can be made shorter than that of the first wire group 120.

The semiconductor device 700 has a general configuration as described above.

Next, a method of manufacturing the semiconductor device 700 will be described below with reference to FIGS. 1 to 15.

First, a substrate 100 as shown in FIGS. 3 and 4 is prepared.

As shown in FIGS. 3 and 4, for example, the substrate 100 is formed of a glass epoxy substrate having a thickness of 0.2 mm. As shown in FIG. 3, the substrate 100 has a plurality of product formation portions 101 arranged in the form of a matrix. For example, the product formation portions 101 arranged in the form of a matrix includes two 4x4 areas 102a and 102b, each of which includes 16 product formation portions. Each of the product formation portions 101 corresponds to one substrate 100 of the semiconductor device 700 shown in FIGS. 1 and 2. The aforementioned connection pads 103, lands 104, and internal wiring lines 105 (not shown in FIG. 3 or 4) are formed on each of the product formation portions 101.

Furthermore, a frame portion 106 is formed around the areas 102a and 102b, in which the product formation portions 101 are formed in the form of a matrix. Positioning holes 107 are formed in the frame portion 106 at predetermined intervals for conveyance and positioning. Dicing lines 108 are formed between the product formation portions 101.

Next, semiconductor chips 109 are mounted on the substrate 100.

Specifically, the substrate 100 is placed on a die bonding apparatus (not shown) in a state in which the connection pads 103 face upward.

After the substrate 100 has been placed on the apparatus, the semiconductor chips 109 are mounted on the adhesive portion 701 by using the die bonding apparatus (not shown). Then the adhesive portion 701 is hardened by heating or the like. Thus, die bonding is completed.

The semiconductor chips 109 are placed into such positions that the shortest distance 122 between the side 114c and the side 116c is shorter than the shortest distance 124 between the side 114a and the side 116a.

After the semiconductor chips 109 have been mounted on the substrate 100, the substrate 100 is placed on a wire bonding apparatus (not shown).

After the substrate 100 has been placed on the apparatus, ends of the wires 110 are connected to the electrode pads 112 (see FIG. 1) with the wire bonding apparatus (not shown) by



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ultrasonic thermocompression bonding. Then other ends of the wires **110** are connected to the connection pads **103** by ultrasonic thermocompression bonding so that the wires are curved into predetermined loop shapes (see FIGS. 5 and 6).

At that time, the wires **110** are connected so that the wire length of the second wire groups **118** is shorter than that of the first wire groups **120** (see FIGS. 1 and 2).

Next, the substrate **100** on which the semiconductor chips **109** have been mounted is placed on a molding apparatus **300**.

As shown in FIG. 7, the molding apparatus **300** has a metal mold tool including an upper mold **301** and a lower mold **302**. The upper mold **301** comprises a cavity **303** formed in a surface facing the lower mold **302**. The lower mold **302** comprises a recessed portion **304** formed in a surface facing the upper mold **301**. The substrate **100** is mounted on the recessed portion **304** of the lower mold **302**.

As shown in FIG. 8, the substrate **100** that has been subjected to wire bonding (see FIG. 5) is placed within the recessed portion **304** of the lower mold **302** (see FIG. 7).

At that time, the substrate **100** is arranged such that the second wire groups **118** are located near air vents **312** while the first wire groups **120** are located near gates **305**.

Subsequently, as shown in FIG. 8, the substrate **100** is sealed by the upper mold **301** and the lower mold **302**. Since the present embodiment employs a MAP method, the cavity **303** has such a size as to cover all of the product formation portions **101** in the lump. In the present embodiment, the cavity **303** is divided into two areas corresponding to the areas **102a** and **102b**. Then a tablet **306** (resin tablet) is supplied into a pot of the lower mold **302** and melted by heating.

Next, as shown in FIG. 9, the molten sealing resin **307** is injected into the cavity **303** (see FIG. 8) through the gates **305** with a plunger **308**.

At that time, the molten sealing resin **307** is injected from the first wire groups **120** toward the second wire groups **118**, i.e., from the side of the long wires toward the side of the short wires. Therefore, it is possible to prevent a wire sweep and a wire short circuit, which would be caused by the injected resin.

When the sealing resin **307** is injected, the resin is filled so as to spread laterally due to the wires **110** near the gates **305**. Therefore, the sealing resin **307** can be injected from the gates **305** without any wire short circuit even though the wire groups of long wires are located near the gates **305**.

After the cavity **303** has been filled with the sealing resin, curing is conducted at a predetermined temperature, e.g., at 180° C. Thus, the sealing resin **307** is hardened so as to form a sealer **401** (see FIG. 2).

Then the substrate **100** is removed from the molding apparatus **300** (metal mold tool). A reflow process is performed at a predetermined temperature, e.g., at 240° C. As a result, the sealer **401** is completely hardened.

Thus, as shown in FIGS. 10 and 11, there is formed an intermediate structure **400** of a semiconductor device in which two sealers **401a** and **401b** are respectively formed in the two areas **102a** and **102b** of the product formation portions **101** on the substrate **100** (see FIG. 3). Furthermore, the sealing resin **307** is removed from the gates **305**, runners **309**, and culls **310**, which are connected to the sealers **401a** and **401b** of the intermediate structure **400**.

Next, as shown in FIGS. 12 and 13, solder balls **500** are mounted on the lands **104** of the substrate **100** so as to form bump electrodes, which serve as external terminals.

Specifically, a suction mechanism (not shown), which comprises a plurality of suction holes corresponding to the locations of the lands **104** on the substrate **100**, is used to hold

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the solder balls **500** within the suction holes. The solder balls **500** being held are correctively mounted onto the lands **104** of the substrate **100** via flux.

After the solder balls **500** have been mounted on all of the product formation portions **101**, a reflow process is performed on the substrate **100**. Thus, bump electrodes (external terminals) are formed.

Next, the substrate **100** on which the solder balls **500** have been mounted is placed on a substrate dicing apparatus (not shown).

After the substrate **100** has been placed on the apparatus, the substrate **100** is cut along the dicing lines **108** (see FIG. 3) as shown in FIGS. 14 and 15. Thus, the product formation portions **101** (see FIG. 3) are individually separated from each other. Specifically, the sealers **401a** and **401b** of the substrate **100** are bonded to a dicing tape **600** via an adhesive layer (not shown) so that the dicing tape **600** supports the substrate **100**. Subsequently, the substrate **100** is cut longitudinally and laterally along the dicing lines **108** by a dicing blade (not shown) of the dicing apparatus, so that the product formation portions **101** are individually cut and separated from each other. When an individual product formation portion **101** separated from other product formation portions **101** is picked up from the dicing tape **600**, a semiconductor device **700** as shown in FIGS. 1 and 2 can be obtained.

Thus, according to the first embodiment, the semiconductor device **700** comprises the first wire group **120** and the second wire group **118** provided so as to respectively stride across the sides **116a** and **116c** of the semiconductor chip **109**, which are opposed to each other. The wire length of the second wire group **118** is shorter than that of the first wire group **120**. At the time of production, the sealer **401** is formed by injecting the sealing resin **307** from the side of the first wire group **120** toward the side of the second wire group **118**.

Accordingly, a wire sweep and a wire short circuit can be prevented from occurring even if the flow rate of the sealing resin **307** is increased near the air vents **312** by entrainment of the sealing resin **307** when the sealing resin **307** is being injected.

Next, a second embodiment of the present invention will be described with reference to FIGS. 16 and 17.

In the second embodiment, a semiconductor chip set **800a** is provided by mounting a plurality of semiconductor chips on the substrate of the first embodiment.

In the second embodiment, elements having the same function as in the first embodiment are denoted by the same reference numerals. The following description is focused on differences between the first embodiment and the second embodiment.

As shown in FIGS. 16 and 17, a semiconductor device **700a** includes a substrate **100** and a lower semiconductor chip **109a** mounted on the substrate **100**.

The substrate **100** includes connection pads **167a** and **167c** arranged along the side **114a** and the side **114c**, respectively.

The substrate **100** also includes connection pads **169a** and **169c** arranged along the side **114a** and the side **114c**, respectively. The connection pads **169a** and **169c** are located outside of the connection pads **167a** and **167c**, respectively.

The lower semiconductor chip **109a** has a rectangular shape on the plane with four sides **131a**, **131b**, **131c**, and **131d**.

Meanwhile, the lower semiconductor chip **109a** includes electrode pads **173a** and **173c** arranged along the side **131a** and the side **131c**, respectively. The electrode pads **173a** and **173c** are connected to the connection pads **167a** and **167c**, respectively, by wires **110a**.

An upper semiconductor chip 109b is stacked on the lower semiconductor chip 109a via an adhesive portion 701 such as a DAF. The lower semiconductor chip 109a and the upper semiconductor chip 109b constitute the semiconductor chip set 800a.

The size of the upper semiconductor chip 109b is smaller than that of the lower semiconductor chip 109a. The upper semiconductor chip 109b is arranged on the lower semiconductor chip 109a so that the electrode pads 173a and 173c of the lower semiconductor chip 109a are exposed.

The upper semiconductor chip 109b also has a rectangular shape on the plane with four sides 133a, 133b, 133c, and 133d, which correspond to the sides 131a, 131b, 131c, and 131d of the lower semiconductor chip 109a, respectively.

Furthermore, the upper semiconductor chip 109b includes electrode pads 171a and 171c arranged along the side 133a (first side) and the side 133c (second side), respectively.

The electrode pads 171a and 171c are arranged such that intervals 151 between the electrode pads 171c are greater than intervals 153 between the electrode pads 171a.

The electrode pads 171a are connected to the connection pads 169a by a first wire group 135. The electrode pads 171c are connected to the connection pads 169c by a second wire group 137. Thus, the wire intervals of the second wire group 137 are greater than the wire intervals of the first wire group 135.

Since the intervals 151 between the electrode pads 171c are greater than the intervals 153 between the electrode pads 171a, the wire intervals of the second wire group 137 become greater than the wire intervals of the first wire group 135. Therefore, a wire short circuit is less likely to occur.

Furthermore, the shortest distance 122b between the side 133c of the upper semiconductor chip 109b and the side 114c of the substrate 100 is shorter than the shortest distance 124b between the side 133a of the upper semiconductor chip 109b and the side 114a of the substrate 100. Moreover, the shortest distance 122a between the side 133c of the upper semiconductor chip 109b and the side 131c of the lower semiconductor chip 109a is shorter than the shortest distance 124a between the side 133a of the upper semiconductor chip 109b and the side 131a of the lower semiconductor chip 109a.

With such an arrangement, the wire length of the second wire group 137 can be made shorter than that of the first wire group 135 as with the first embodiment.

Meanwhile, the wire length of the wires 110a of the lower semiconductor chip 109a is shorter than that of wires 110b of the upper semiconductor chip 109b. Therefore, the wires 110a of the lower semiconductor chip 109a have less risk of a wire short circuit as compared to the wires 110b of the upper semiconductor chip 109b. Accordingly, the wires 110a of the lower semiconductor chip 109a are configured to have an equal wire length.

In the second embodiment, when the sealing resin 307 is to be injected, an injection direction of the sealing resin 307 is selected in consideration of the arrangement of the wires 110b of the upper semiconductor chip 109b, which is likely to be influenced by the risk of a wire short circuit.

Specifically, when the sealing resin 307 is to be injected, the substrate 100 is set on the molding apparatus 300 so that the second wire group 137 faces the air vents 312 while the first wire group 135 faces the gates 305. The sealing resin 307 is injected from the side of the first wire group 135 toward the side of the second wire group 137.

Thus, even in a case of a multi-chip package (MCP) type semiconductor device 700a having a plurality of semiconductor chips mounted thereon, a wire sweep and a wire short circuit can be prevented from occurring without an increase

of the size of the semiconductor device 700a if the flow rate of the sealing resin 307 is increased near the air vents 312 by entrainment of the sealing resin 307 when the sealing resin 307 is being injected, as with the first embodiment.

Furthermore, when the sealing resin 307 is injected, the sealing resin 307 is filled so as to spread laterally due to the wires near the gates 305. Therefore, by arranging the first wire group 135 of long wires near the gates 305 as with the first embodiment, the sealing resin 307 can be injected from the gates 305 without any wire short circuit even though the long wires are located near the gates 305.

Thus, according to the second embodiment, the semiconductor device 700a has the first wire group 135 and the second wire group 137 provided so as to respectively stride across the sides 133a and 133c of the upper semiconductor chip 109b, which are opposed to each other. The wire length of the second wire group 137 is shorter than that of the first wire group 135. At the time of production, the sealer 401 is formed by injecting the sealing resin 307 from the side of the first wire group 135 toward the side of the second wire group 137.

Accordingly, the same advantageous effects as in the first embodiment can be attained.

Furthermore, according to the second embodiment, the lower semiconductor chip 109a and the upper semiconductor chip 109b are stacked on the substrate 100 of the semiconductor device 700a. The lower semiconductor chip 109a and the upper semiconductor chip 109b constitute the semiconductor chip set 800a.

Therefore, the second embodiment is applicable to an MCP type semiconductor device.

Moreover, according to the second embodiment, the intervals 151 between the electrode pads 171c are greater than the intervals 153 between the electrode pads 171a. Accordingly, the intervals of the second wire group 137 become greater than the intervals of the first wire group 135.

As a result, a wire short circuit is less likely to occur as compared to the first embodiment.

Next, a semiconductor device 700b according to a third embodiment will be described below with reference to FIGS. 18 and 19.

In the third embodiment, the wire diameter of the wires 110c of the second wire group 118 is greater than that of the wires 110 of the first wire group 120 of the first embodiment.

In the third embodiment, elements having the same function as in the first embodiment are denoted by the same reference numerals, and the explanation thereof is omitted herein.

As shown in FIGS. 18 and 19, in the semiconductor device 700b, the wire diameter of the wires 110c of the second wire group 118 is greater than that of the wires 110 of the first wire group 120. In other words, wires having a wire diameter greater than the wires 110 are used for the wires 110c.

With this configuration, a wire short circuit is less likely to occur as compared to the case where the wires 110c have the same wire diameter as the wires 110.

Thus, according to the third embodiment, the semiconductor device 700b has the first wire group 120 and the second wire group 118 provided so as to respectively stride across the sides 116a and 116c of the semiconductor chip 109, which are opposed to each other. The wire length of the second wire group 118 is shorter than that of the first wire group 120. At the time of production, the sealer 401 is formed by injecting the sealing resin 307 from the side of the first wire group 120 toward the side of the second wire group 118.

Accordingly, the same advantageous effects as in the first embodiment can be attained.

Furthermore, according to the third embodiment, the wire diameter of the wires **110c** of the second wire group **118** is greater than that of the wires **110** of the first wire group **120** in the semiconductor device **700b**.

Therefore, a wire short circuit is less likely to occur as compared to the first embodiment.

Next, a semiconductor device **700c** according to a fourth embodiment will be described below with reference to FIGS. **20** and **21**.

In the fourth embodiment, wires are provided only on one side of the upper semiconductor chip **109b** of the second embodiment.

In the fourth embodiment, elements having the same function as in the second embodiment are denoted by the same reference numerals, and the explanation thereof is omitted herein.

As shown in FIGS. **20** and **21**, the electrode pads **171a** are provided only along the side **133a** of the upper semiconductor chip **109b** in the semiconductor device **700c**. Wires **139** are connected to the electrode pads **171a** so as to stride across the side **133a**.

Meanwhile, the substrate **100** includes connection pads **103** arranged along the side **114a**, **114b**, **114c**, and **114d** and connection pads **181** arranged only along the side **114a**. The connection pads **181** are located outside of the connection pads **103**.

The connection pads **103** are connected to the electrode pads **112** of the lower semiconductor chip **109a** via the wires **110a**. The connection pads **181** are connected to the electrode pads **171a** by the wires **139**.

Thus, the wires **139** may be provided only on one side of the upper semiconductor chip **109b**.

In this case, the wires **139** correspond to the first wire group. Some of the wires **110a** provided on the lower semiconductor chip **109a** that stride across the side **131c**, which is located on an opposite side of the side **133c** to the side **133a**, correspond to the second wire group.

In this case, the semiconductor device **700c** is placed on the molding apparatus **300** so that the wires **139** (the side **133a**) face the gates **305** while the side **131c** faces the air vents **312**. The sealer **401** is formed by injecting the sealing resin **307** from the side of the wires **139** toward the side **131c**.

Thus, according to the fourth embodiment, the semiconductor device **700c** includes the wires **139** provided so as to stride across the side **133a** of the upper semiconductor chip **109b**. At the time of production, the sealer **401** is formed by injecting the sealing resin **307** from the side of the wires **139**.

Accordingly, the same advantageous effects as in the first embodiment can be attained.

Furthermore, according to the fourth embodiment, the wires **139** are provided only on one side of the semiconductor device **700c**.

Therefore, advantageous effects equivalent to or higher than those of the second embodiment can be attained.

Although the inventions has been described above in connection with several preferred embodiments thereof, it will be appreciated by those skilled in the art that those embodiments are provided solely for illustrating the invention, and should not be relied upon to construe the appended claims in a limiting sense.

For example, in the above embodiments, the present invention is applied to a semiconductor device comprising one or two semiconductor chips mounted on a substrate. Nevertheless, the present invention is also applicable to any semiconductor device having different wire lengths, such as a semiconductor device comprising three or more semiconductor chips stacked thereon.

Furthermore, in the above embodiments, the substrate is formed of a glass epoxy substrate. Nevertheless, the substrate may be formed of a ceramic substrate. Alternatively, a flexible substrate formed of a polyimide substrate may be used instead.

What is claimed is:

1. A semiconductor device comprising:

a substrate having a first side and a second side opposite the first side;

a first semiconductor chip on the substrate;

a second semiconductor chip on the first semiconductor chip, the second semiconductor chip having plural first bonding pads spaced a first distance apart along a third side of the second semiconductor chip facing the first side and plural second bonding pads spaced a second distance apart along a fourth side of the second semiconductor chip opposite the third side, the first side being spaced farther from the third side than the second side is spaced from the fourth side;

a plurality of first wires that each directly connect the substrate to respective ones of the first bonding pads, and a plurality of second wires that each directly connect the substrate to respective ones of the second bonding pads, each wire of the plurality of first wires being longer than each wire of the plurality of second wires; and

a sealing resin covering the first and second semiconductor chips, the plurality of first wires, and the plurality of second wires,

wherein the second semiconductor chip is completely overlapped with the first semiconductor chip in plan view.

2. The semiconductor device of claim 1, wherein the second distance is greater than the first distance.

3. The semiconductor device of claim 2, wherein a quantity of the plural first bonding pads exceeds a quantity of the plural second bonding pads.

4. The semiconductor device of claim 1, wherein the first bonding pads are arrayed in a first line and the second bonding pads are arrayed in a second line parallel to the first line.

5. The semiconductor device of claim 1, wherein the second semiconductor chip is smaller than the first semiconductor chip so that connection pads on the first semiconductor chip are exposed.

6. The semiconductor device of claim 1, wherein the first semiconductor chip has a fifth side facing the first side of the substrate and a sixth side opposite the fifth side, and wherein the fifth side is spaced farther from the third side than the sixth side is spaced from the fourth side.

7. A semiconductor device comprising:

a substrate having a first side and a second side opposite the first side;

a first semiconductor chip on the substrate;

a second semiconductor chip on the first semiconductor chip, the second semiconductor chip having plural first bonding pads spaced a first distance apart along a third side of the second semiconductor chip facing the first side and plural second bonding pads spaced a second distance apart along a fourth side of the second semiconductor chip opposite the third side, the first side being spaced farther from the third side than the second side is spaced from the fourth side;

a first wire group connecting the substrate to the first bonding pads and a second wire group connecting the substrate to the second bonding pads, each wire of the first wire group being longer than each wire of the second wire group; and

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a sealing resin covering the first and second semiconductor chips and the first and second wire groups, wherein the second distance is greater than the first distance,

wherein the substrate comprises plural third bonding pads arrayed along the first side and plural fourth bonding pads arrayed along the first side closer to the first semiconductor chip than the third bonding pads, the first wire group being connected to the third bonding pads, and the fourth bonding pads being connected to the first semiconductor chip, and

wherein the substrate comprises plural fifth bonding pads arrayed along the second side and plural sixth bonding pads arrayed along the second side closer to the first semiconductor chip than the fifth bonding pads, the second wire group being connected to the fifth bonding pads, and the sixth bonding pads being connected to the first semiconductor chip.

8. The semiconductor device of claim 7, wherein third bonding pads are spaced a third distance apart and the fifth bonding pads are spaced a fourth distance apart, the fourth distance being greater than the third distance.

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